

Power Supply Design Seminar

Topic 4 Presentation:

Under the Hood of a Multiphase Synchronous Rectified Boost Converter

Reproduced from
2014 Texas Instruments Power
Supply Design Seminar SEM2100,
Topic 4
TI Literature Number: SLUP324

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Under the Hood of a Multiphase Synchronous Rectified Boost Converter

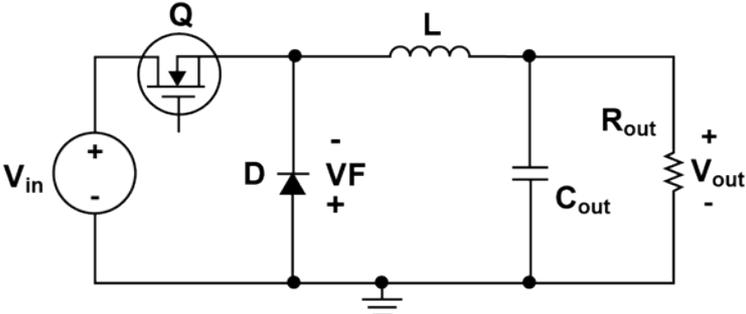
David Baba

Agenda

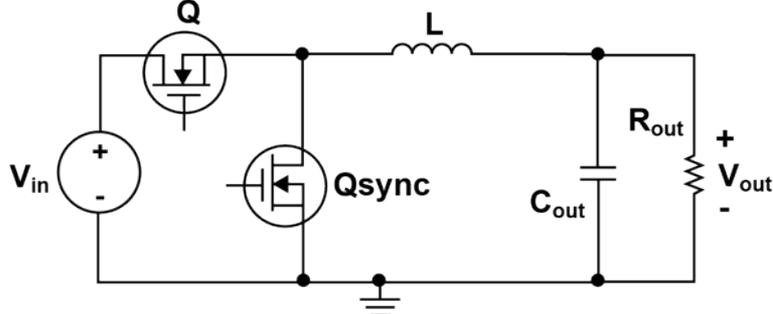
- **Synchronous boost introduction**
 - Deciding how many phases to use
- **Synchronous multiphase boost waveforms**
- **Design example single phase/two phase**
 - Component selection
 - Loss calculations
 - Compensation
- **Results**
- **Summary**

Changing to Synchronous Rectification

Non Synchronous Buck to Synchronous Buck

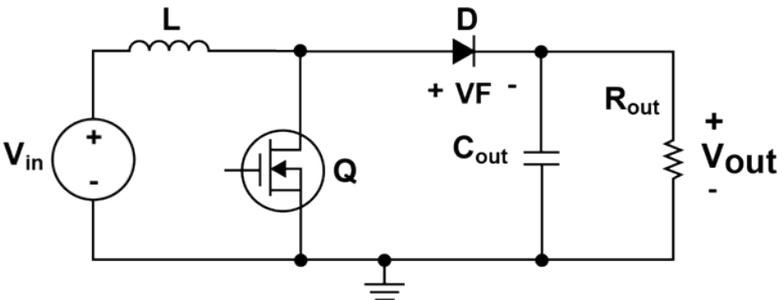


$$\text{Losses} = (1 - D) \times I_{\text{out}} \times VF$$

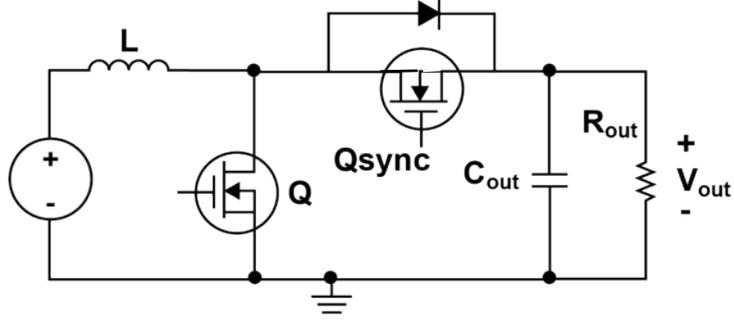


$$\text{Losses} = I_{\text{RMS}}^2 \times RDS_{\text{on}}$$

Non Synchronous to Synchronous Boost



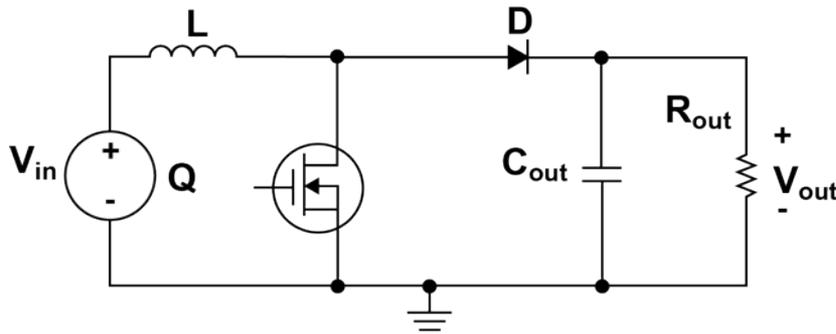
$$\text{Losses} = I_{\text{out}} \times VF$$



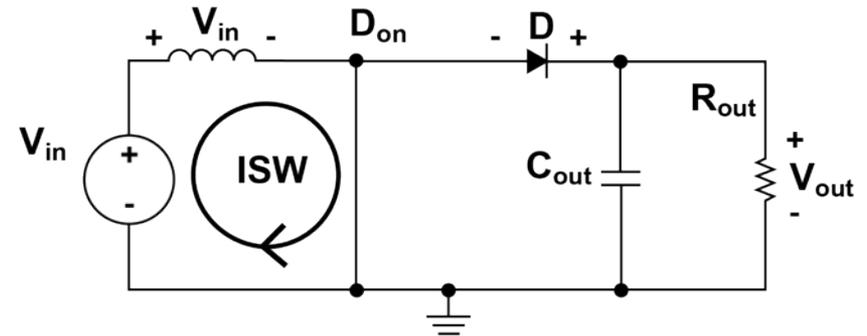
$$\text{Losses} = I_{\text{RMS}}^2 \times RDS_{\text{on}}$$

Boost Converter Basic Operation

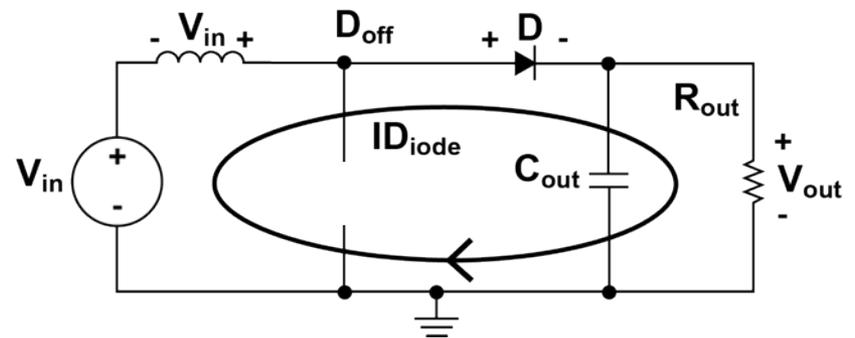
Simple Boost Diagram



Boost During D_{ON} Period

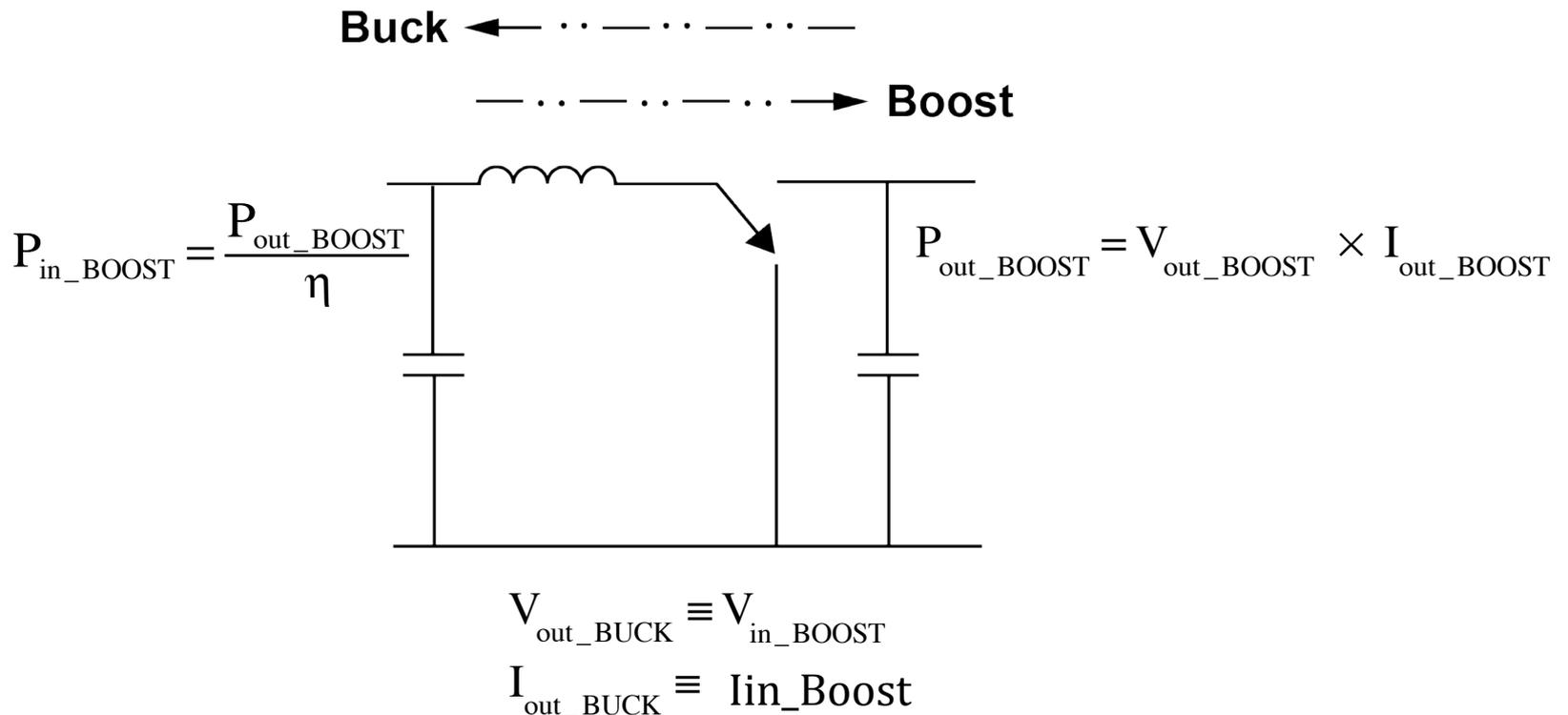


Boost During D_{OFF} Period



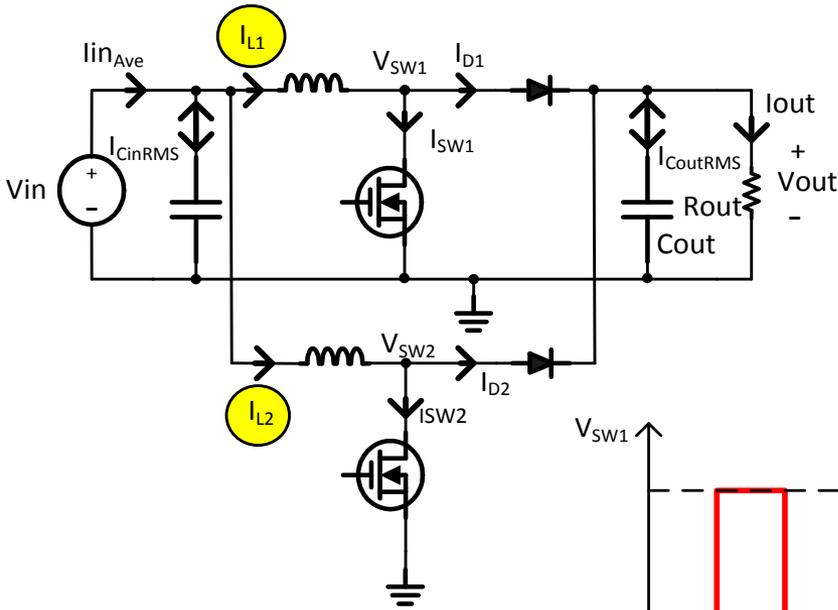
Determine Input Current per Phase

Drawing Comparisons Between Buck and Boost

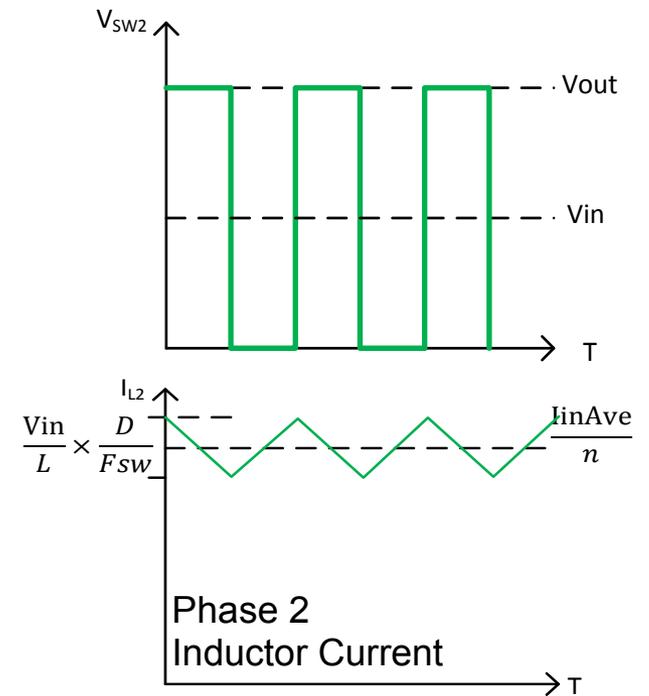
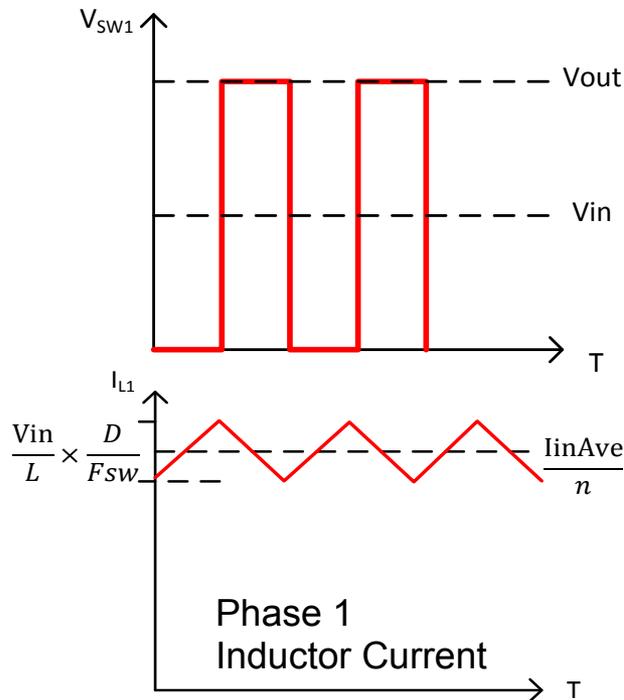


Canonical Schematic

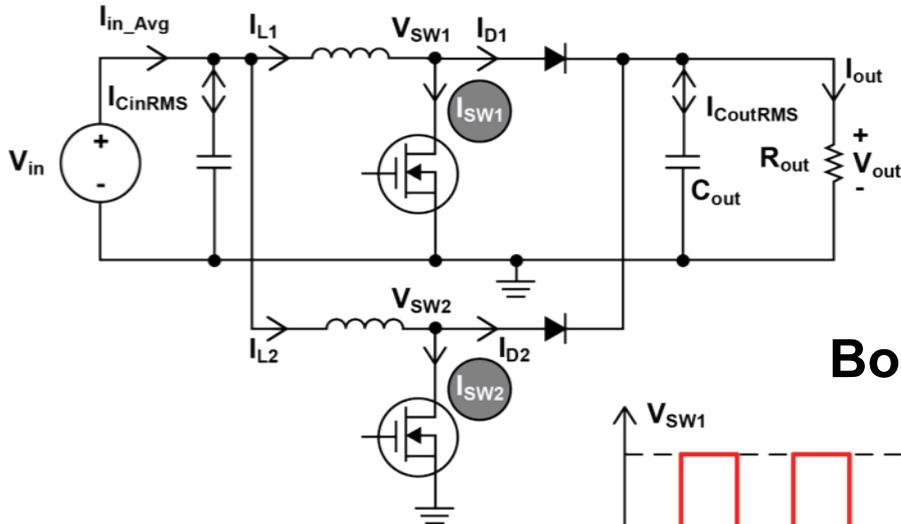
Interleaved Boost Basic Operation



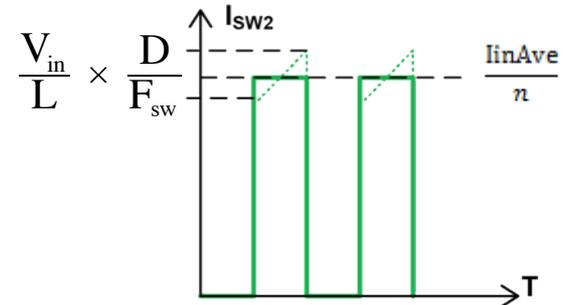
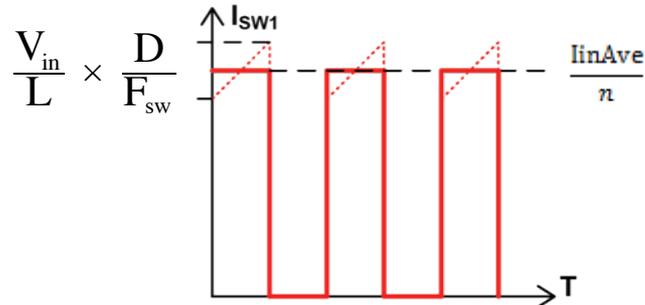
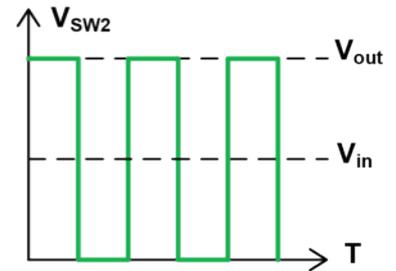
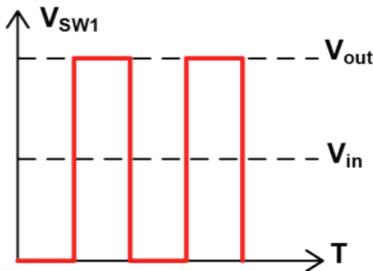
Inductor Currents



Interleaved Boost Basic Operation



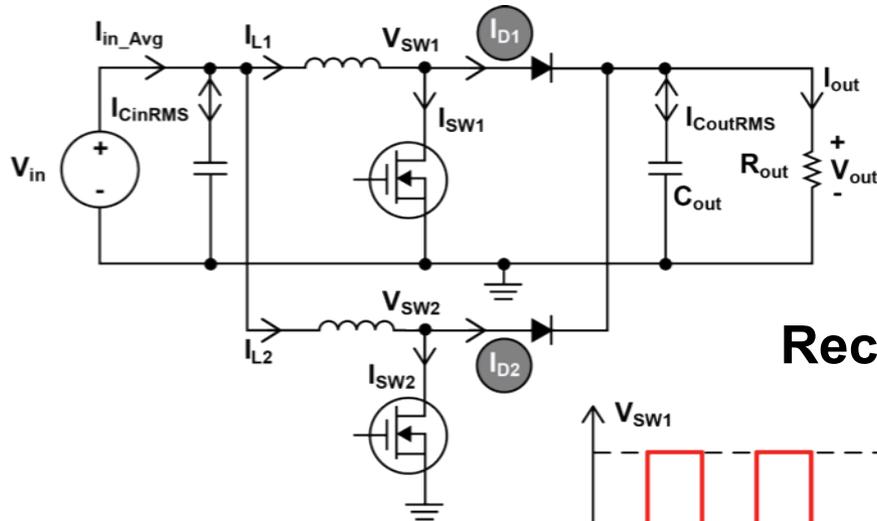
Boost Switch Currents



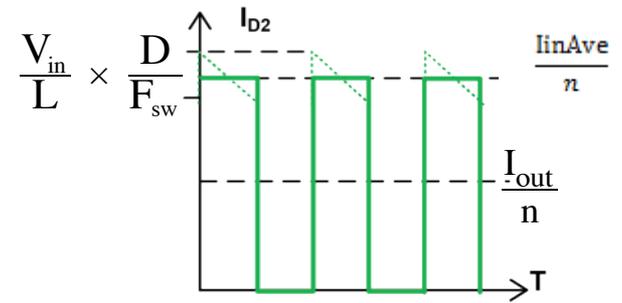
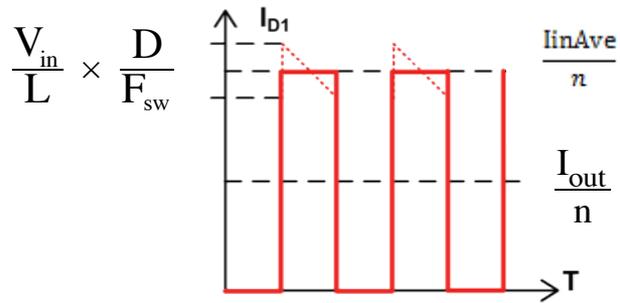
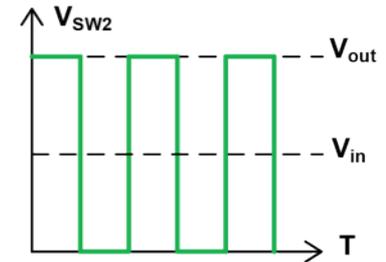
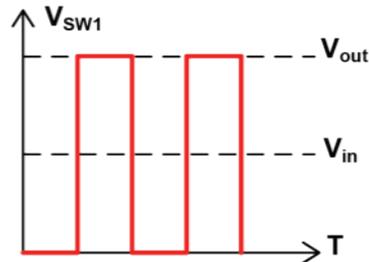
Phase 1 Switch Current

Phase 2 Switch Current

Interleaved Boost Basic Operation



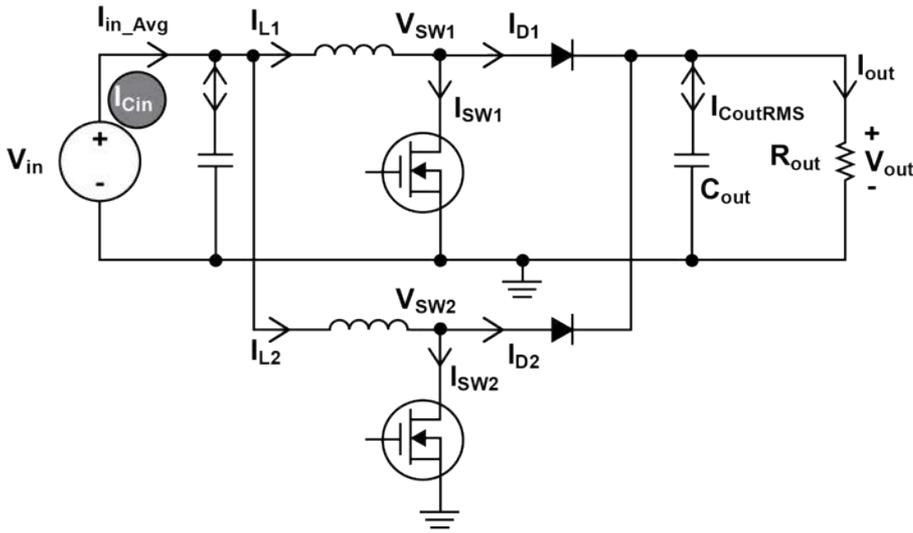
Rectifier Switch Currents



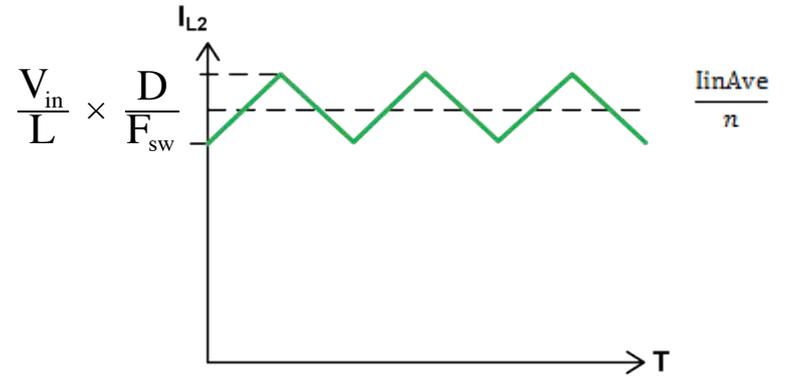
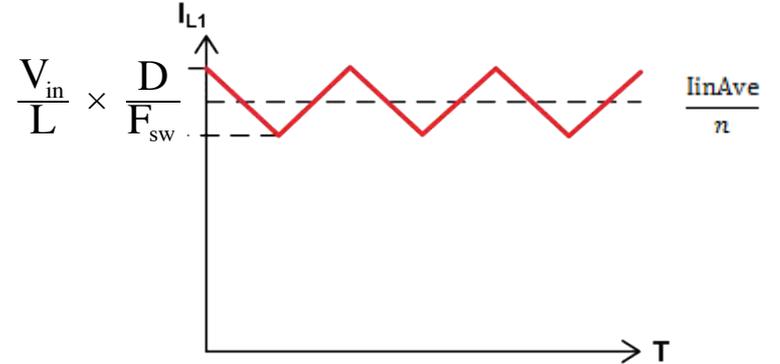
Phase 1 Rectifier Current

Phase 2 Rectifier Current

Interleaved Boost Basic Operation

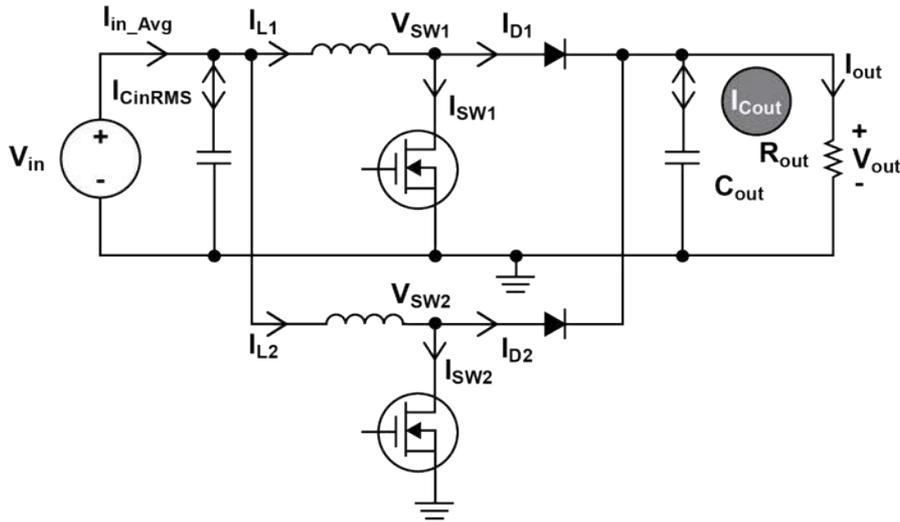


Input Capacitor Currents

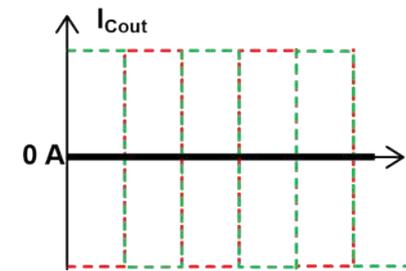
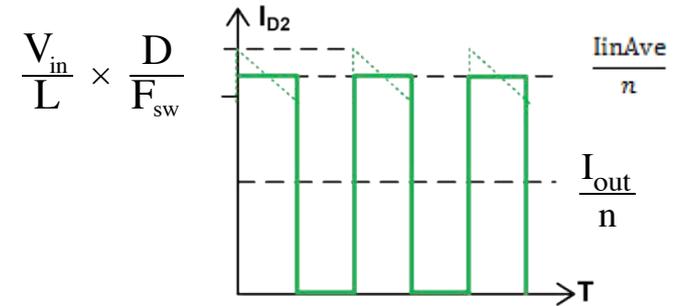
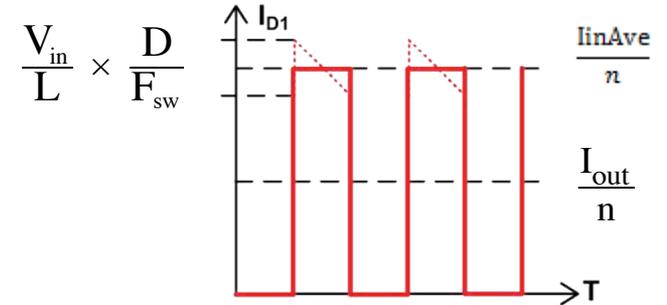


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Ripple currents cancel at 50%

Interleaved Boost Basic Operation



Output Capacitor Currents



Ripple currents cancel at 50%

The Basic Boost Calculations

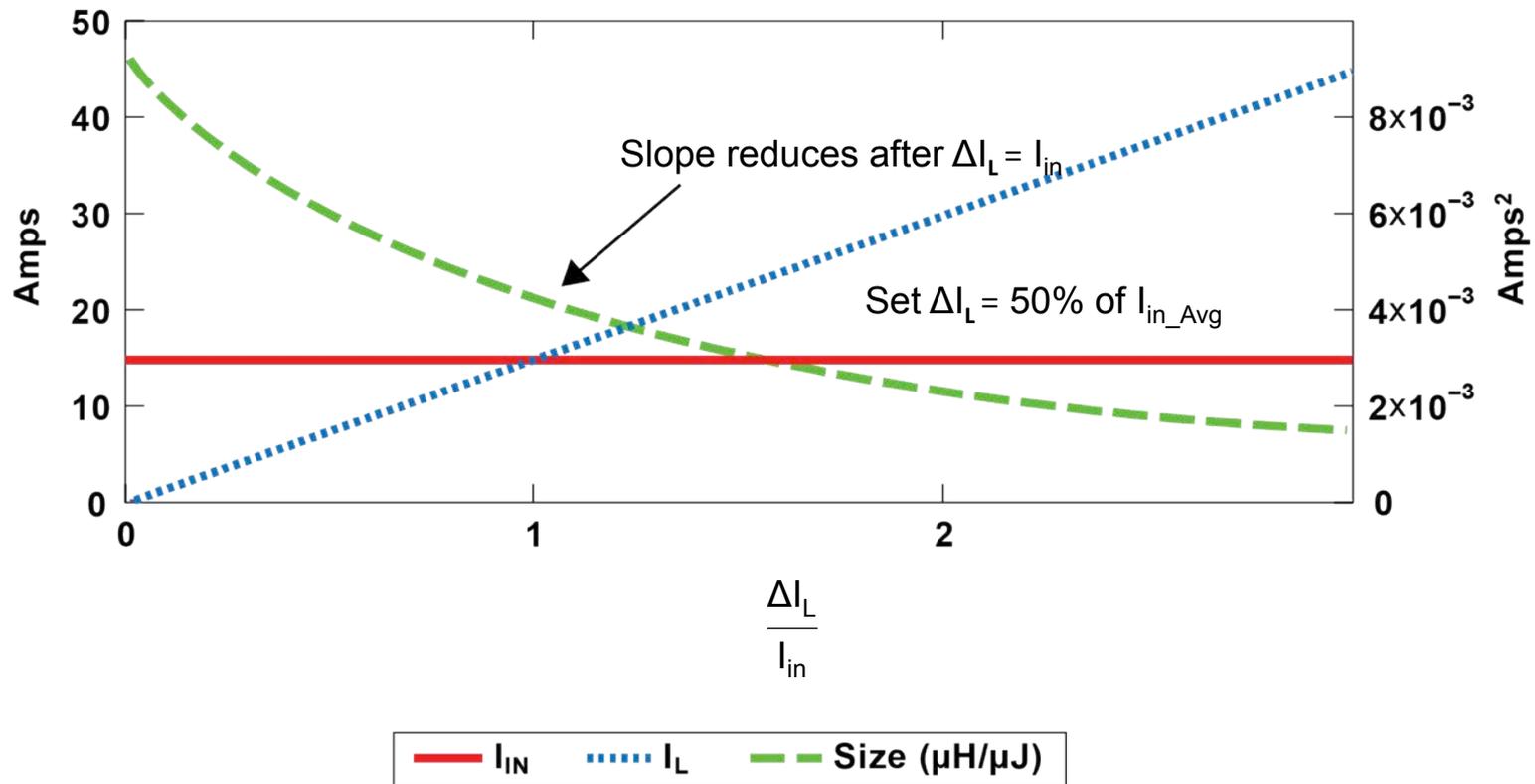
Design Example

- Automotive trunk amplifier
- 14 V_{in}
- 24 V_{out} @ 8 A
- Switching Frequency (F_{sw})
 - 250 kHz (single phase)
 - 125 kHz (two phase) system switching frequency held constant

Equation	Single Phase	Two Phase	Comment
	250 kHz	125 kHz	Per Phase F _{sw}
$\frac{V_{out}}{V_{in}} = \frac{1}{1-D}$			Transfer Function
$D = \frac{V_{out} - V_{in}}{V_{out}}$	D = 0.42	D = 0.42	Rearranging for D
$P_{in} = \frac{P_{out}}{\eta}$	P _{in} = 206 W	P _{in} = 206 W	Efficiency Est. 93%
$I_{in_Avg} = \frac{P_{in}}{V_{in} \times n}$	14.7 ≈ 206 W / 14 V × 1	14.7 ≈ 206 W / 14 V × 2	n = No. Phase

Selecting the Right Inductor and Inductance Calculations

Graph showing size factor as a function of ΔI_L



Boost Inductor Losses

Equation	Single Phase	Two Phase	Comment
$\Delta I_L = 0.5 \times I_{in_Avg}$	$\approx 7.5 \text{ A}$	$\approx 3.5 \text{ A}$	Set ΔI_L to 50% of I_{in_Avg}
$I_{L_peak} = \frac{\Delta I_L}{2} + I_{in_Avg}$	$= 18.5 \text{ A}$	$= 8.4 \text{ A}$	I_{sat} to be set higher than I_{L_peak}
$L = \frac{V_{ind} \times D}{\Delta I_L \times F_{SW}}$	$= 3.16 \mu\text{H}$	$= 13.4 \mu\text{H}$	Boost inductor calculation
$I_{L_RMS} = \sqrt{I_{in_Avg}^2 + \left(\frac{\Delta I_L}{\sqrt{12}}\right)^2}$	$= 14.9 \text{ A}$	$= 7 \text{ A}$	RMS current for DCR Loss
Selected Inductor	Coilcraft XAL1580-302	Coilcraft SER1390-153	2 cores for the two phase
Inductor size	13.2, 14.1, 7.5	13.5, 13.5, 9	Volume of inductor (in mm)
DCR	$3 \text{ m}\Omega$	$14 \text{ m}\Omega$	
$DCR_{loss} = I_{L_RMS}^2 \times DCR$	$= 0.6 \text{ W}$	$= 1.4 \text{ W}$	Total DCR losses
$Coreloss = K_1 \times f^x \times B^y \times V_E$	$= 2.6 \text{ W}$	$= 18 \text{ mW}$	Total from online calculator

AC Inductor Losses

$$\text{Coreloss} = K_1 \times f^x \times B^y \times V_E$$

- K_1 : Constant of the core material
- f : Switching frequency in kHz
 - **Higher frequencies results in higher losses**
- B : Flux density in kGuass
 - **Lower flux density results in lower losses**
- x : Frequency exponent for a specific core material
- y : is the flux exponent for a specific core material
- V_E : Core volume
 - **Larger volume results in more losses**

Boost Converter MOSFET Considerations

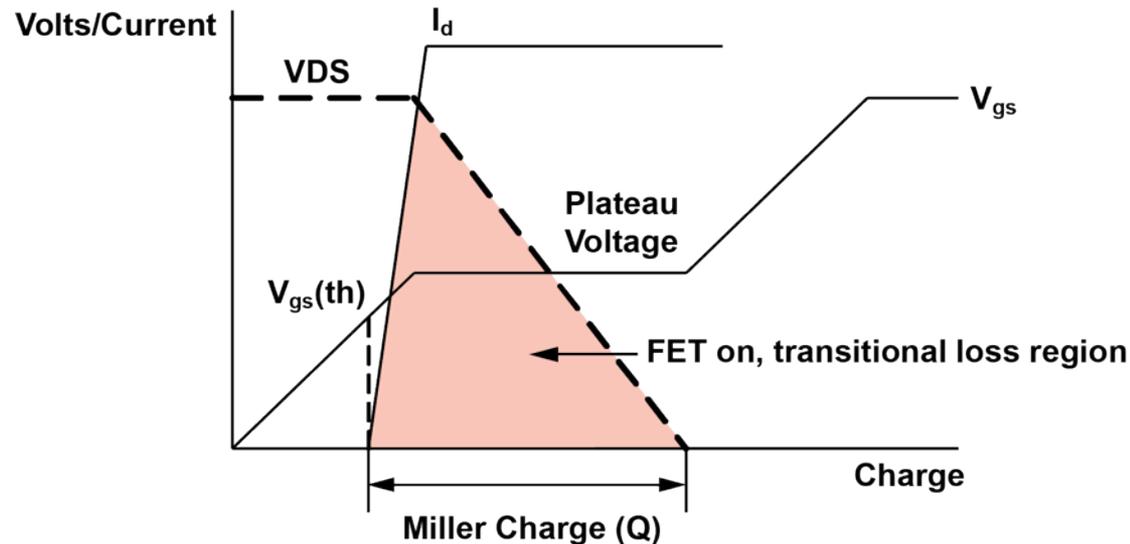
- VDS rating must be greater than output voltage
 - 25% margin is generally acceptable
- Calculate losses to determine suitability
- Losses ideally should be distributed evenly between conduction losses and switching losses
 - Higher RMS currents result in larger conduction losses
 - Higher gate charge results in higher switching losses

Control MOSFET Losses

Equation	Single Phase	Two Phase	Comment
FET Selected	CSD18531Q5A	CSD18531Q5A	RDS _{on} , 3 mΩ, hot 4 mΩ
$I_{FET_RMS} = \sqrt{D} \times I_{in_Avg}$	≈ 9 A	≈ 4.47 A	FET RMS current
$P_{FET_Cond} = I_{FET_RMS}^2 \times RDS_{on}$	≈ 0.3 W	≈ 0.16 W	Total conduction losses
$SW_{TRANSLoss} = V_{out} \times I_{inAVE} \times TSLEW \times FSW$	≈ 0.8 W	≈ 0.4 W	Total transitional losses

Control MOSFET Transitional Losses

Transitional Losses at Turn On



$$SW_{\text{TRANSLoss}} = V_{\text{out}} \times I_{\text{in_Avg}} \times T_{\text{SLEW}} \times F_{\text{SW}}$$

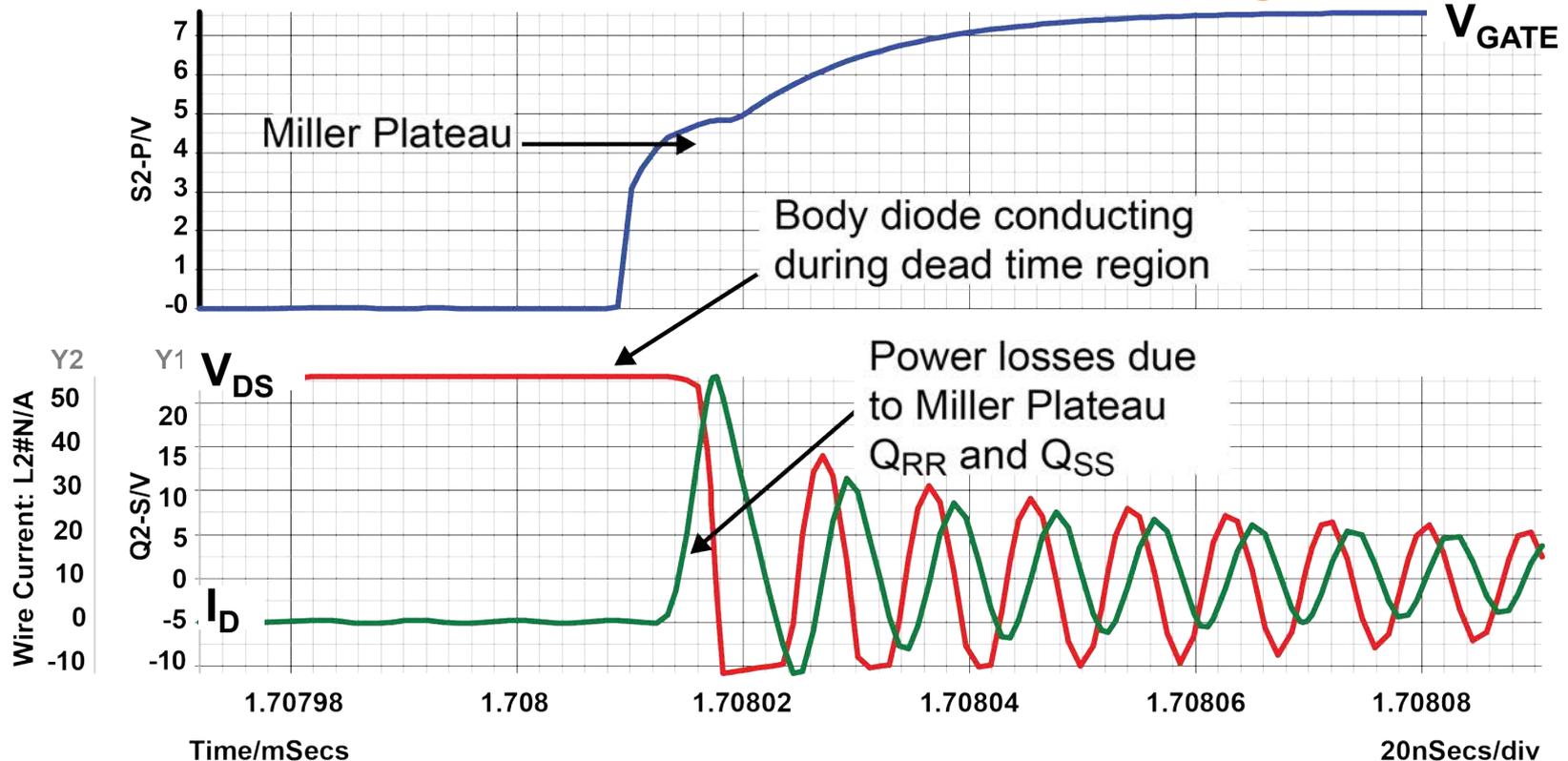
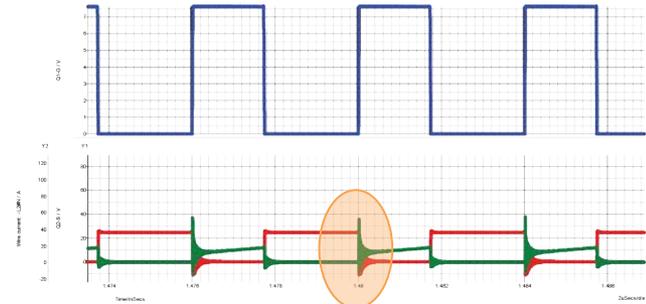
- Use triangular approximation
 - $1/2 \times \text{base} \times \text{height}$
 - For worst case, the “1/2” drops out

Synchronous MOSFET Losses

Equation	Single Phase	Two Phase	Comment
FET Selected	CSD18531Q5A	CSD18531Q5A	RDS _{on} , 3 mΩ, hot 4 mΩ
$I_{\text{FET_RMS}} = \sqrt{1-D} \times I_{\text{in_Avg}}$	≈ 11.2 A	≈ 5.3 A	FET RMS current
$\text{FETCond} = I_{\text{(FET_RMS)}}^2 \times \text{RDS}_{\text{on}}$	≈ 0.44 W	≈ 0.22 W	Conduction losses
$Q_{\text{OSSLoss}} = \frac{Q_{\text{OSS}}}{2} \times V_{\text{out}} \times F_{\text{SW}}$	≈ 0.2 W	≈ 0.2 W	Q _{OSS} losses for both FETs
$Q_{\text{RR_Loss}} = Q_{\text{RR}} \times V_{\text{out}} \times n \times F_{\text{SW}}$	≈ 0.6 W	≈ 0.6 W	100 nC of Q _{RR} losses in boost FET
$I_{\text{C_Loss}} = V_{\text{in}} \times n \times \left\{ \left(Q_{\text{Gtot}} \times F_{\text{SW}} \right) + I_{\text{Q}} \right\}$	≈ 0.18 W	≈ 0.33 W	Loss total in IC

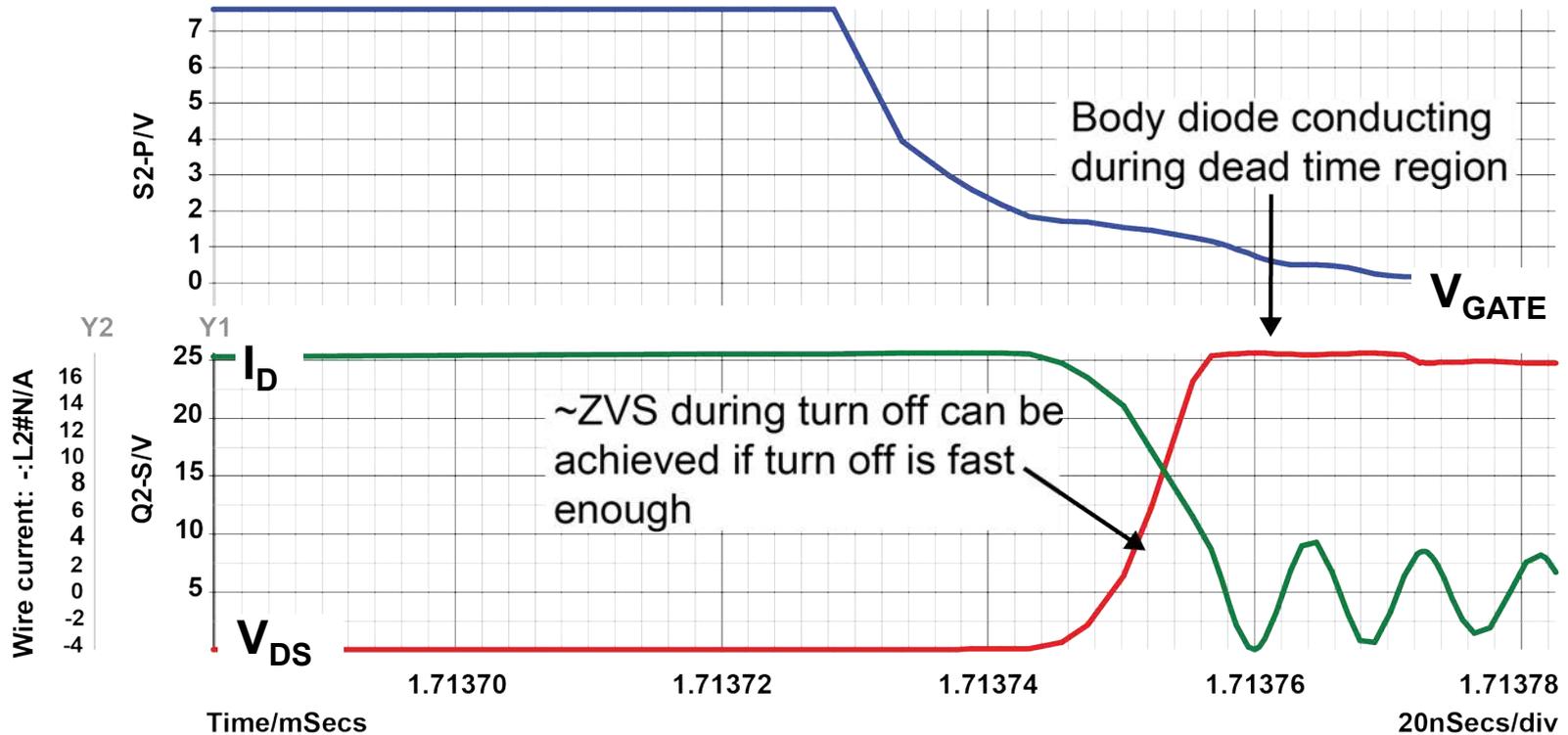
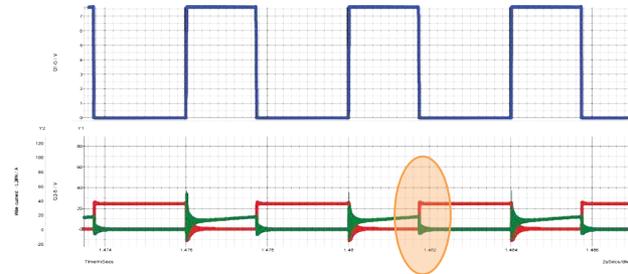
Boost Converter FET Switching

Control FET: Turn On



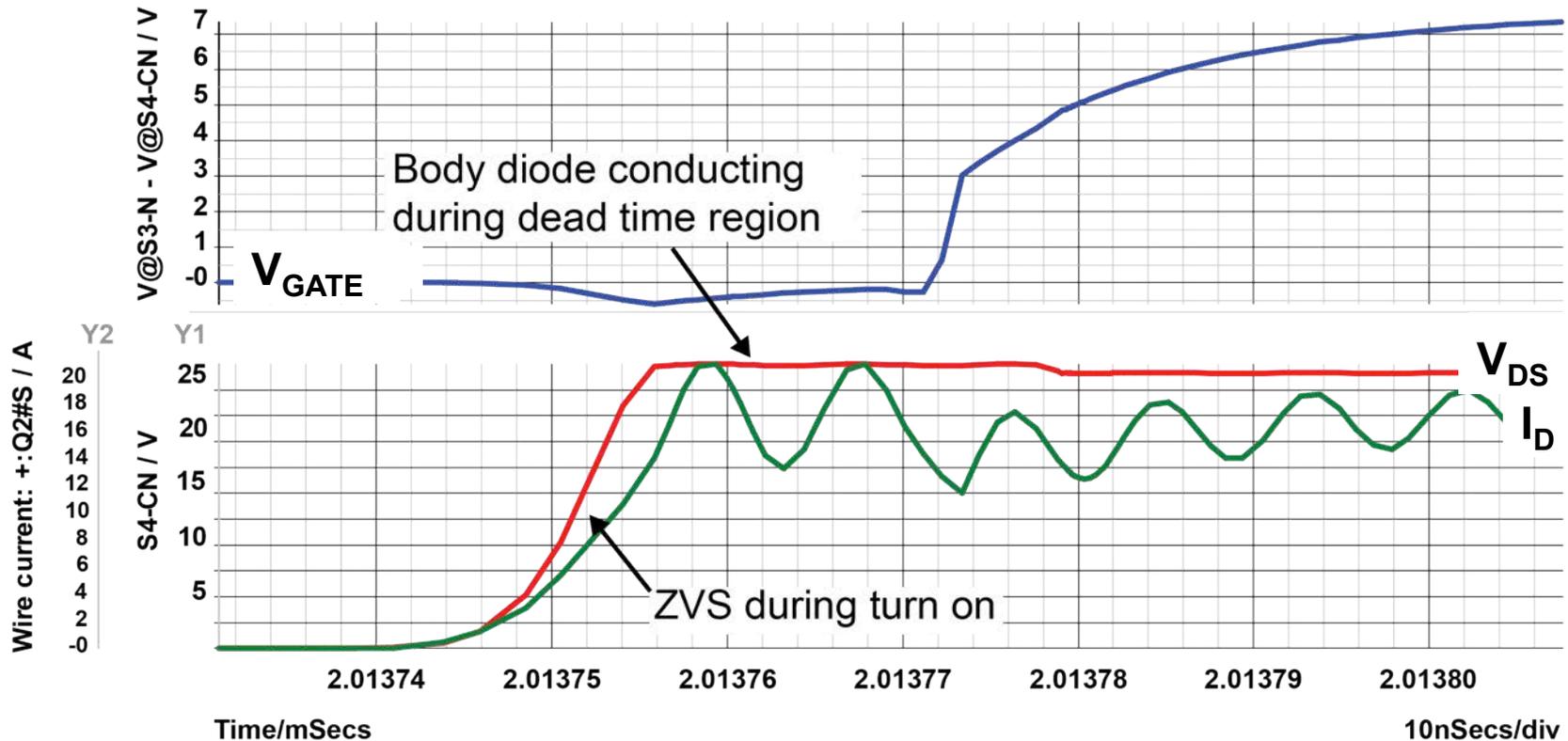
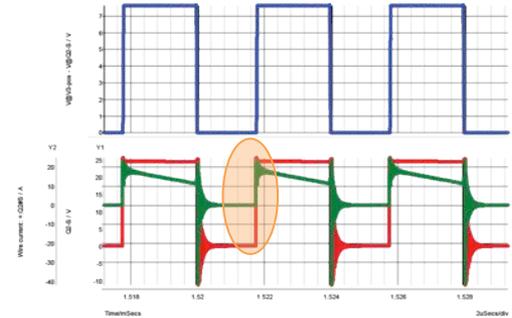
Boost Converter FET Switching

Control FET: Turn Off



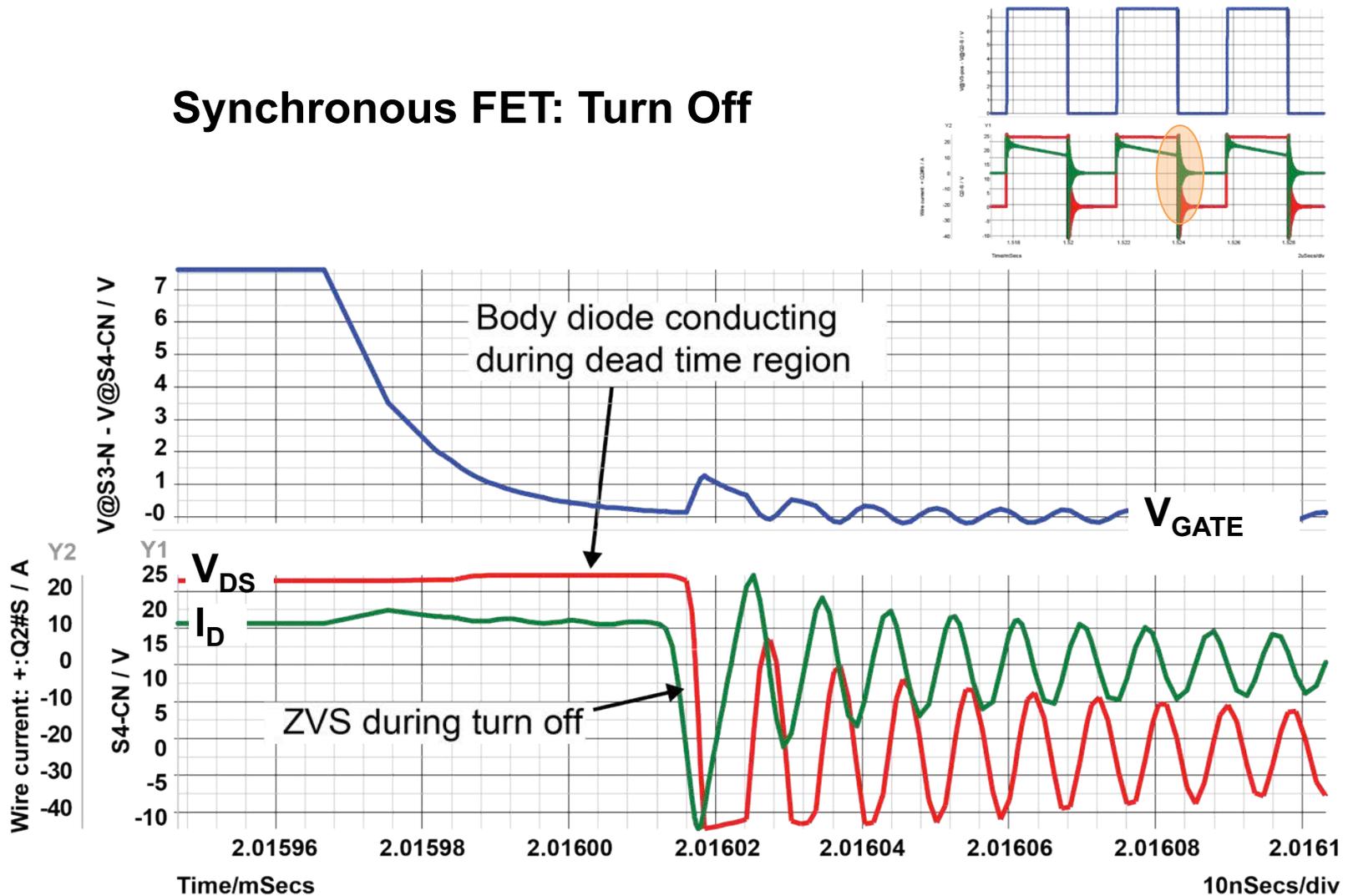
Boost Converter FET Switching

Synchronous FET: Turn On



Boost Converter FET Switching

Synchronous FET: Turn Off



Input/Output RMS Ripple Current

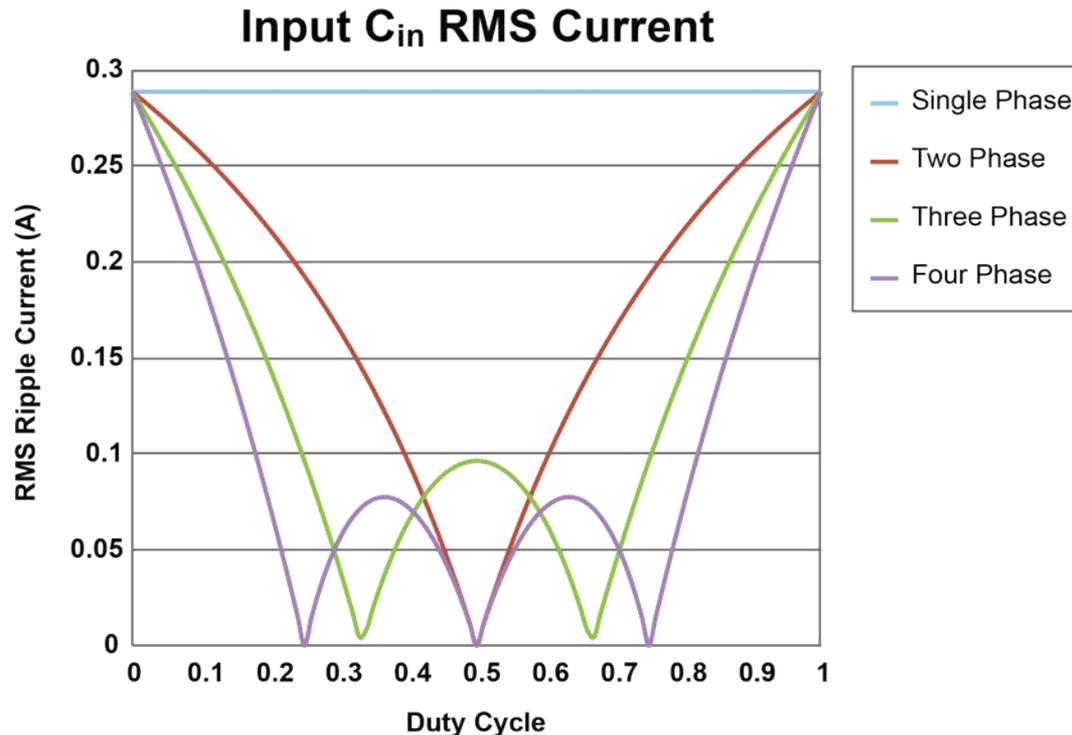
Single Phase	Two Phase	Comment
$I_{C_in_RMS} = \frac{\Delta I_L}{\sqrt{12}} = 2.1 \text{ A}$	$I_{C_in_RMS} = \frac{\Delta I_L}{\sqrt{12}} \times \frac{1-2D}{1-D} = 0.9 \text{ A}$	Two phase D < 0.5
$I_{C_out_RMS} \approx I_{out} \times \sqrt{\frac{D}{(1-D)}} = 6.7 \text{ A}$	$I_{C_out_RMS} \approx \frac{I_{out}}{\sqrt{2}} \times \frac{\sqrt{D \times (1-2D)}}{(1-D)}$ = 2.5 A	Two phase D < 0.5
$\Delta I_{C_out} \approx I_{in_Avg} = 14.75 \text{ A}$	$\Delta I_{C_out} \approx I_{in_Avg} = 6.8 \text{ A}$	Pk-Pk ripple current in C _{OUT}
2 x PCV1E391MCL2GS	1 x PCV1E391MCL2GS	390 μF electrolytic selected

Output Ripple Voltage Calculations

Single Phase	Two Phase	Comment
$V_{C_out_Ripple} = \frac{\Delta I_{C_out} \times D}{F_{SW} \times C_{out}} = 29 \text{ mV}$	$V_{C_out_Ripple} = \frac{\Delta I_{C_out} \times D}{F_{SW} \times C_{out}} = 29 \text{ mV}$	Ripple voltage due to charge C_{out}
$\Delta I_{Cout} \approx \frac{I_{out}}{n \times (1-D)} = 13.7 \text{ A}$	$\Delta I_{Cout} \approx \frac{I_{out}}{n \times (1-D)} = 6.89 \text{ A}$	
$V_{C_out_Ripple_ESR} = \Delta I_{C_out} \times C_{out_ESR}$ $= 144 \text{ mV}$	$V_{C_out_Ripple_ESR} = \Delta I_{C_out} \times C_{out_ESR}$ $= 144 \text{ mV}$	Ripple voltage due to C_{outESR}
$V_{out_Ripple} =$ $\sqrt{V_{C_out_Ripple}^2 + V_{C_out_Ripple_ESR}^2}$ $= 147 \text{ mV}$	$V_{out_Ripple} =$ $\sqrt{V_{(C_out_Ripple)}^2 + V_{(C_out_Ripple_ESR)}^2} = 155 \text{ mV}$	Total ripple voltage

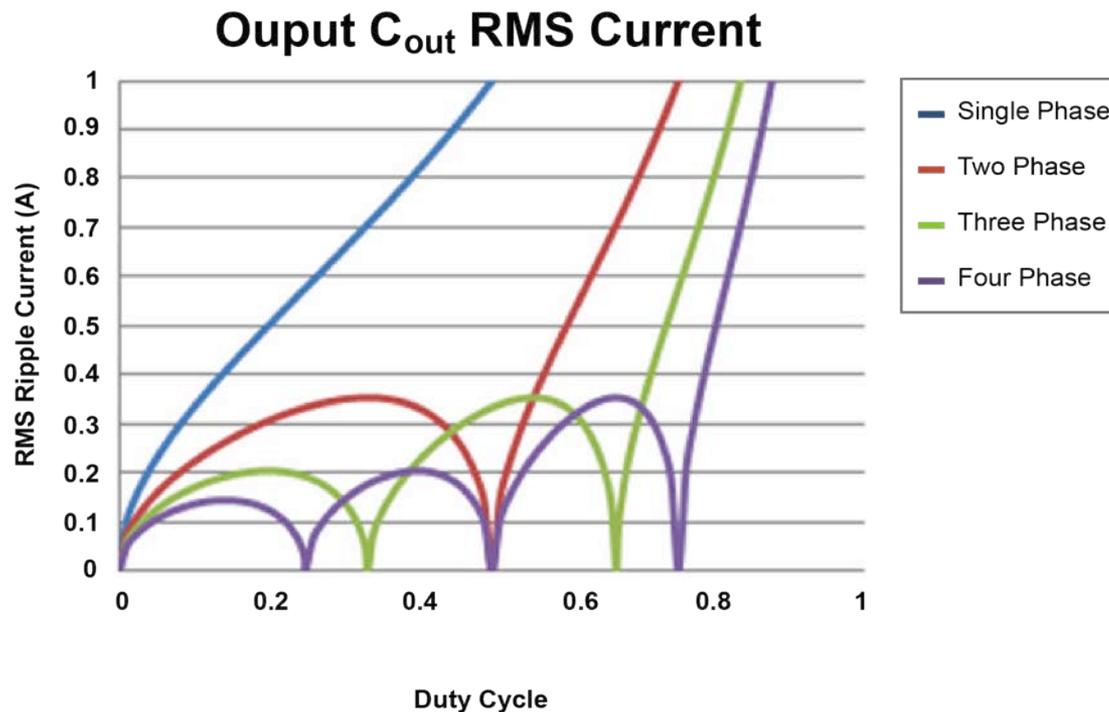
C_{in} RMS Ripple Current Rating Multiphase Boost

- Comparison of ripple current cancelation
- Boost convertor 1, 2, 3 and 4 phase approach
- Using a ΔI_L of 1 A peak to peak



C_{out} RMS Ripple Current Rating Multiphase Boost

- Approximation
- Output ripple current cancelation for a boost convertor
- I_{out} of 1 A using a 1, 2, 3 and 4 phase approach



C_{in} RMS Ripple Current

Condition	Single Phase
$0 < D < 1$	$\frac{\Delta I_L}{\sqrt{12}}$
Condition	Two Phase
$0 < D < 0.5$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{1-2D}{1-D}$
$0.5 < D < 1$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{2D-1}{D}$
Condition	Three Phase
$0 < D < 0.33$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{1-3D}{1-D}$
$0.33 < D < 0.66$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{(1-3D) \times (3D-2)}{3D \times (1-D)}$
$0.66 < D < 1$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{3D-2}{D}$

C_{in} RMS Ripple Current

Condition	Four Phase
$0 < D < 0.25$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{1-4D}{1-D}$
$0.25 < D < 0.5$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{(1-4D) \times (4D-2)}{4D \times (1-D)}$
$0.5 < D < 0.75$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{(3-4D) \times (4D-2)}{4D \times (1-D)}$
$0.75 < D < 1$	$\frac{\Delta I_L}{\sqrt{12}} \times \frac{4D-3}{D}$

C_{out} RMS Ripple Current*

Condition	Single Phase
$0 < D < 1$	$I_{OUT} \times \sqrt{\frac{D}{(1-D)}}$
Condition	Two Phase
$0 < D < 0.5$	$\frac{I_{OUT}}{\sqrt{2}} \times \frac{\sqrt{D \times (1-2D)}}{(1-D)}$
$0.5 < D < 1$	$\frac{I_{OUT}}{2} \times \frac{\sqrt{2 \times (2D-1)}}{\sqrt{1-D}}$
Condition	Three Phase
$0 < D < 0.33$	$\frac{I_{OUT}}{\sqrt{3}} \times \frac{\sqrt{D \times (1-3D)}}{(1-D)}$
$0.33 < D < 0.66$	$\frac{I_{OUT}}{3} \times \frac{(3D-2) \times (1-3D)}{(1-D)}$
$0.66 < D < 1$	$\frac{I_{OUT}}{3} \times \frac{\sqrt{3D-2}}{\sqrt{1-D}}$

*Approximations

C_{out} RMS Ripple Current*

Condition	Four Phase
$0 < D < 0.25$	$\frac{I_{OUT}}{2} \times \frac{\sqrt{D \times (1-4D)}}{(1-D)}$
$0.25 < D < 0.5$	$\frac{I_{OUT}}{2} \times \frac{\sqrt{(4D-2) \times (1-4D)}}{2 \times (1-D)}$
$0.5 < D < 0.75$	$\frac{I_{OUT}}{2} \times \frac{\sqrt{(4D-2) \times (3-4D)}}{2 \times (1-D)}$
$0.75 < D < 1$	$\frac{I_{OUT}}{2} \times \frac{\sqrt{4D-3}}{\sqrt{1-D}}$

*Approximations

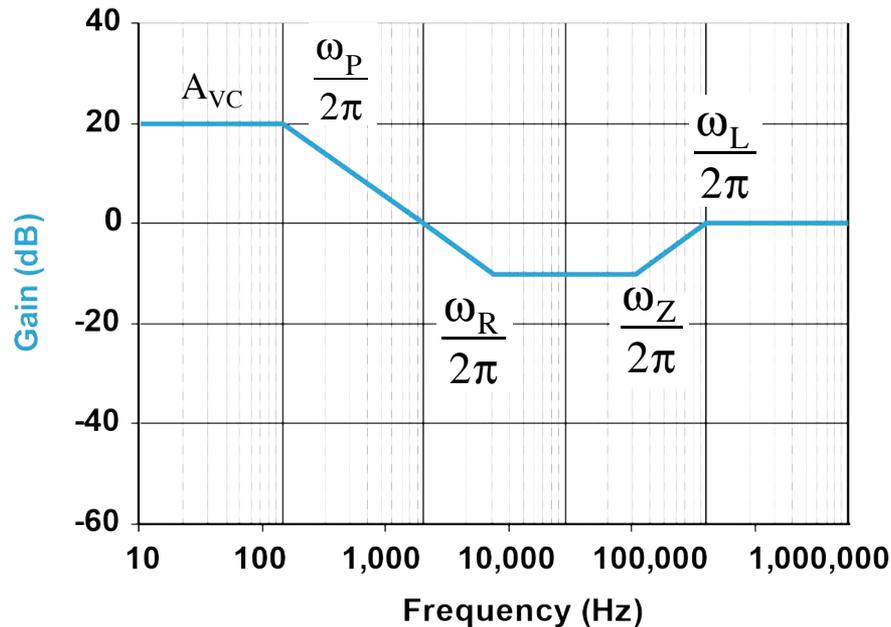
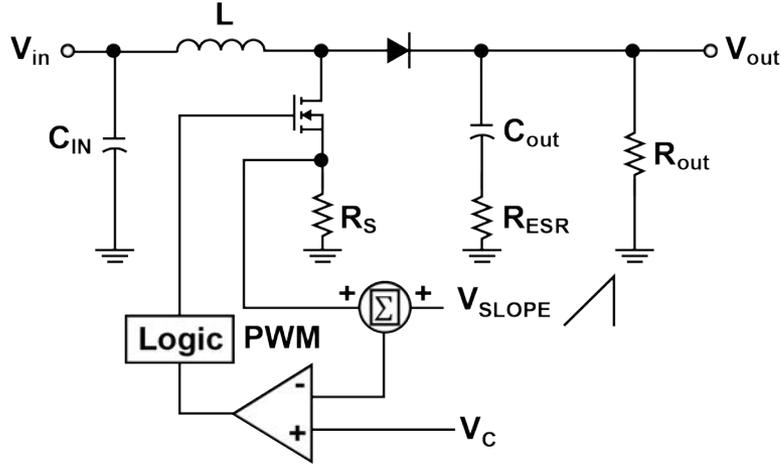
Loop Stability of a Current Mode Boost

- Current mode control modifies the complex conjugate double pole to two separate poles
 - The inductor pole pushes to a higher frequency
- Typically use current mode control (LM5122)
- Right Half Plane Zero (RHPZ)
 - RHPZ causes sudden decrease in the 1-D period due to control loop increasing D for sudden load step
 - Adds additional phase drop of negative 90° phase shift
- Cross over frequency below RHPZ frequency to avoid additional phase shift
- For current mode control, duty cycles approaching 0.5 and beyond require modification to the current sense to avoid subharmonic oscillation

Loop Stability of a Dual Phase Current Mode Boost

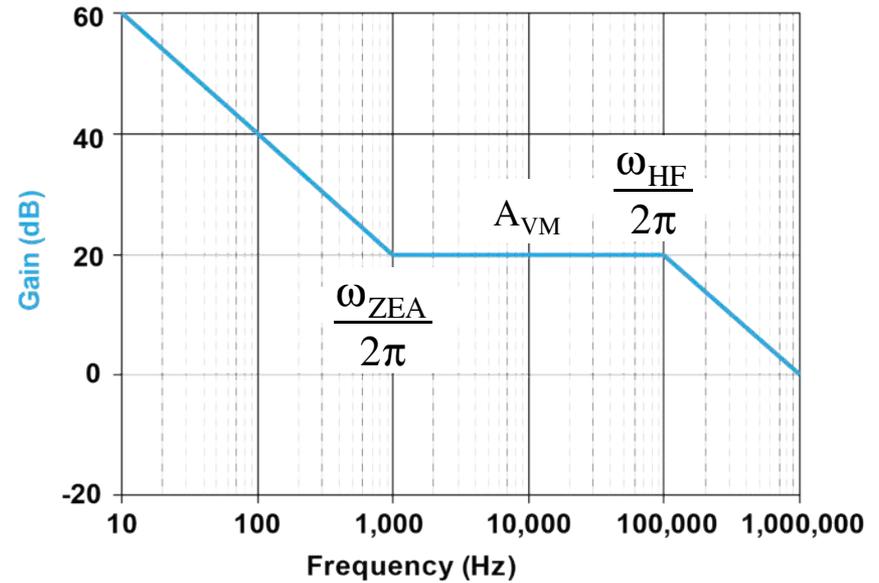
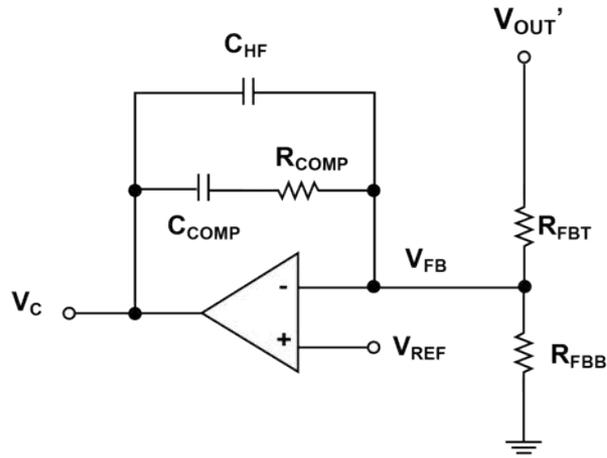
- Adjustments to accommodate an interleaved configuration
- Divide down the output capacitor by number of phases
 - C_{out} becomes 195 μF from 390 μF
- Multiply the output capacitor ESR by number of phases ESR
 - ESR becomes 40 $\text{m}\Omega$, from 20 $\text{m}\Omega$
- Multiply R_{out} by number of phases
 - R_{out} becomes 6 Ω from 3 Ω
 - All other elements stay the same

Current Mode Boost Power Stage



Variable	Equation
$\frac{\hat{V}_{OUT}}{\hat{V}_C}$	$A_{VC} \times \frac{\left(1 - \frac{s}{\omega_R}\right) \times \left(1 + \frac{s}{\omega_Z}\right)}{\left(1 + \frac{s}{\omega_P}\right) \times \left(1 + \frac{s}{\omega_L}\right)}$
R_I	$A_{CS} \times R_S$
A_{VC}	$\approx R_{out} \times n \times \frac{(1-D)}{2 \times R_I}$
ω_P	$\approx \frac{2}{C_{out} \times R_{out}}$
ω_L	$= \frac{K_M \times R_I}{L}$
K_M	$\approx \frac{V_{out}}{V_{SLOPE}}$
ω_Z	$= \frac{1}{C_{out} \times R_{ESR}}$
ω_R	$= \frac{R_{out} \times n \times (1-D)^2}{L}$
V_{SLOPE}	$\frac{(V_{out} - V_{in}) \times R_i}{L \times f_{SW}}$

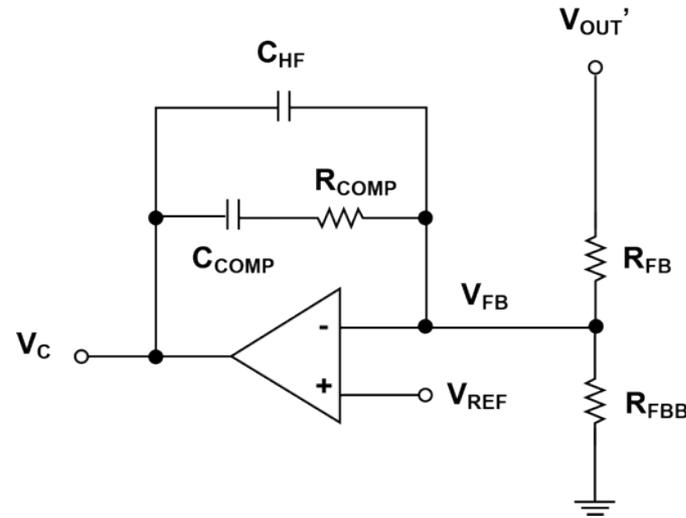
Type II Error Amplifier



$$\frac{\omega_{ZEA}}{2\pi} = \frac{\omega_C}{2\pi \times 10}$$

$$\frac{\omega_{HF}}{2\pi} = \frac{\omega_R}{2\pi}$$

Type II Error Amplifier



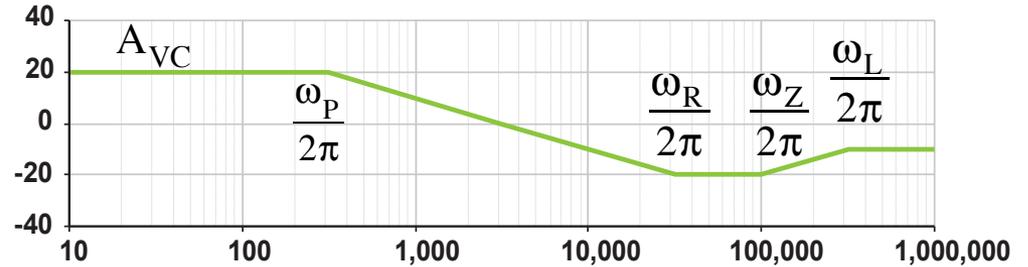
Variable	Single Phase	Two Phase	Comment
R_{FBT}	10 k Ω	10 k Ω	Choose value between 2 k Ω 100 k Ω
D_{MAX}	= 0.625	= 0.625	$= \frac{V_{out} - V_{in_Min}}{V_{out}}$, $V_{in_Min} = 9V$
R_I	= 40 m Ω	= 80 m Ω	$A_{CS} \times R_S$
G_{M_Mod}	= 9.375	= 4.688	$= \frac{1 - D_{max}}{R_I}$

Boost Compensation Approach

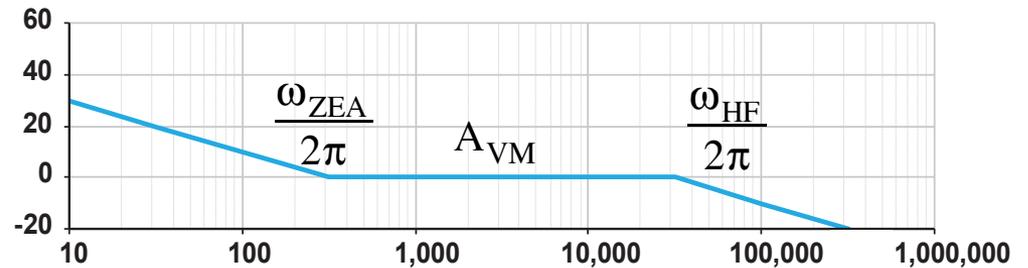
Variable	Single Phase	Two Phase	Comment
RHPZ	$\approx 52 \text{ kHz}$	$\approx 21 \text{ kHz}$	$= \frac{R_{\text{out}} \times n \times (1-D)}{L \times 2\pi}$
F_C	$\approx 12.5 \text{ kHz}$	$\approx 5 \text{ kHz}$	$= \frac{\text{RHPZ}}{4}$
ω_C	$\approx 12.5 \text{ kHz} \times 2\pi$	$\approx 5 \text{ kHz} \times 2\pi$	$= \frac{\omega_R}{4}$
A_{VM}	$= 4.4$	$= 1$	$= \frac{\omega_C \times \frac{C_{\text{out}}}{n}}{G_{M_Mod}}$
R_{COMP}	$= 44 \text{ k}\Omega$	$= 10 \text{ k}\Omega$	$= A_{VM} \times R_{FBT}$
C_{COMP}	$\approx 2.8 \text{ nF}$	$\approx 27 \text{ nF}$	$C_{COMP} = \frac{1}{R_{COMP} \times \omega_{ZEA}}$
C_{HF}	$\approx 68 \text{ pF}$	$\approx 720 \text{ pF}$	$C_{HF} = \frac{1}{R_{COMP} \times \omega_{HF}}$

Asymptotic

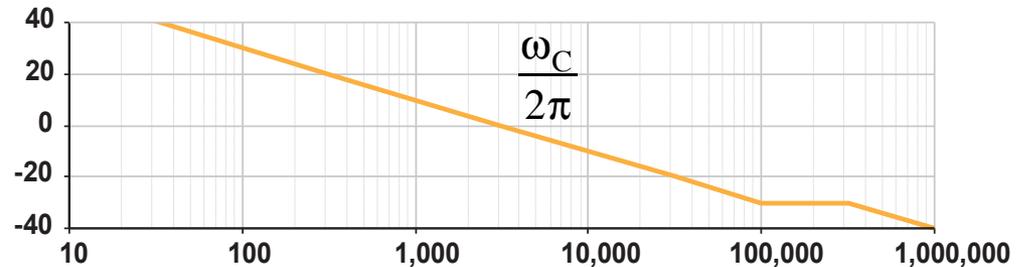
Power Stage Current Mode Boost



Type II Error Amplifier



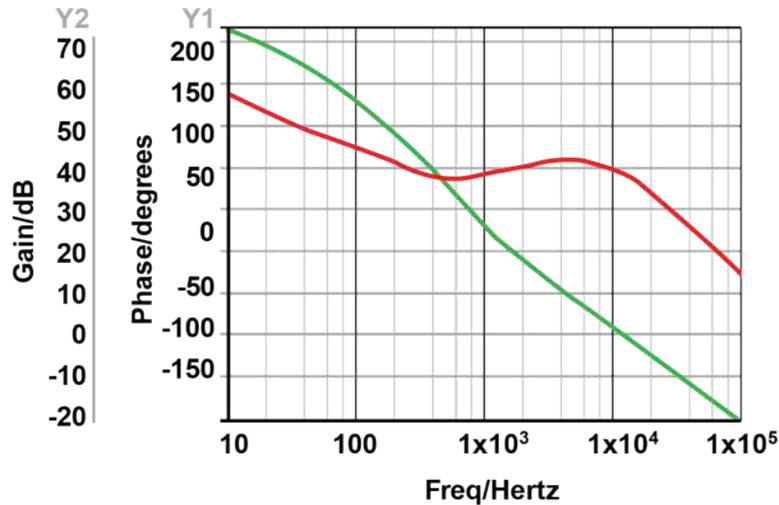
Control Loop



Compensation Results Single Phase

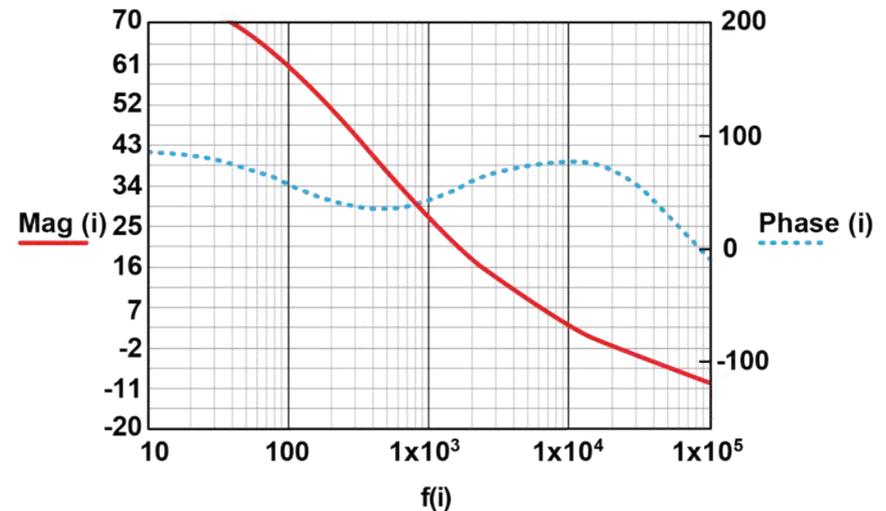
Simulation results

- A crossover frequency of ~ 13 k and a PM of ~ 50 degrees



MathCAD results

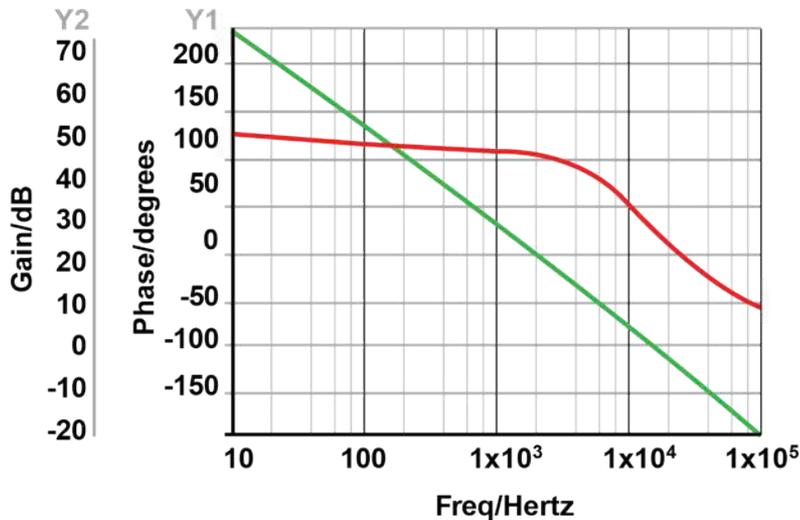
- F_C of ~ 13 k and a PM of ~ 75 degrees



Dual Phase Compensation Results

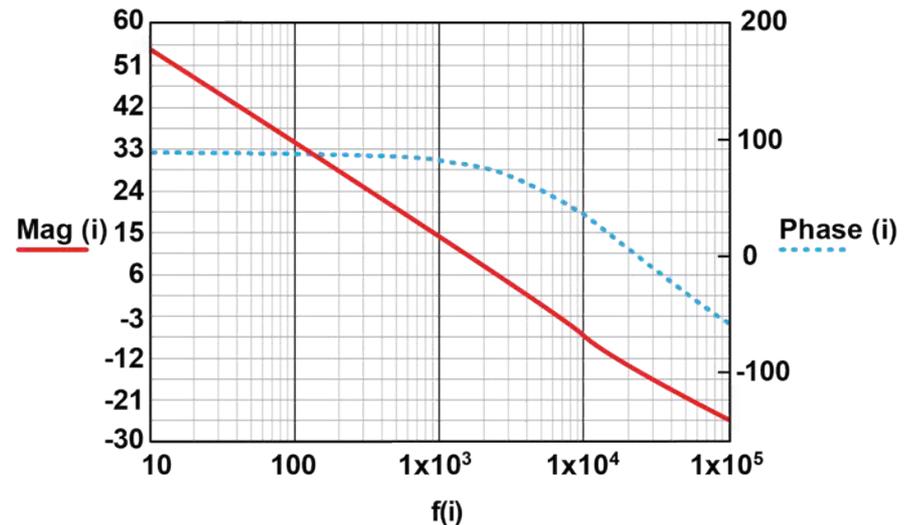
Simulation results (Simplis)

- Shows an F_C of ~5 kHz and a PM of ~56 degrees



Mathcad results

- Mathcad result correlate well to simulation showing an F_C of ~5 kHz and a PM of ~60 degrees



Summary of Results

Parameter	Single Phase	Dual Phase
Per phase switching frequency	250 kHz	125 kHz
Inductance value	3 μ H	15 μ H
I_{sat}	15 A	9 A
Energy $1/2 \times L \times I^2$	337.5 μJ	1.215 mJ
Inductor DCR losses	0.6 W	1.4 W Total
Inductor core losses	2.6 W	0.018 W Total
R_{sense}	4 m Ω	8 m Ω
R_{sense} losses	0.9 W	0.8 W Total
Boost FET conduction losses	0.3 W	0.16 W Total
Boost FET transitional losses	0.8 W	0.4 W Total
FET Q_{OSS} losses	0.2 W	0.2 W Total
Q_{RR} losses	0.6 W	0.6 W
Synchronous FET conduction losses	0.44 W	0.22 W
I_C losses	0.182 W	0.336 W
Total losses	~6.097	~3.734W
Calculated efficiency	W ~97%	~98%
C_{in} RMS ripple current rating	2.1 A	0.9 A
C_{out} RMS ripple current rating	6.7 A	2.5 A
C_{in}	22 μ F	22 μ F
C_{out}	780 μ F	390 μ F
F_C	12.5 kHz	5 kHz

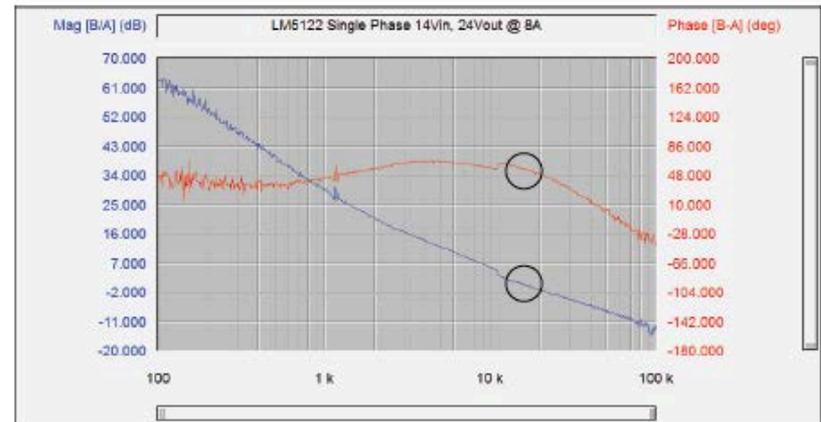
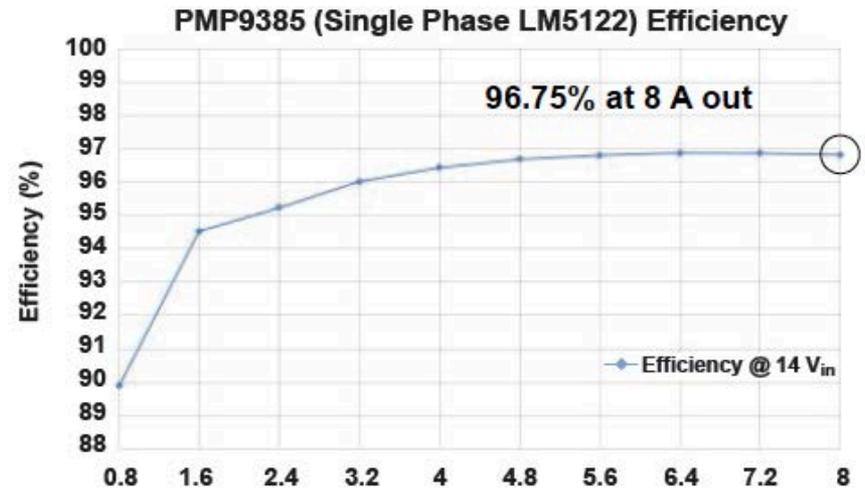
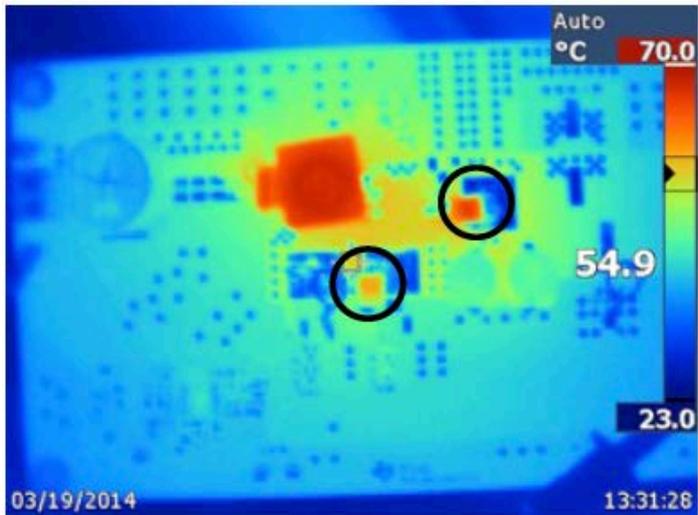
Summary of Results

Component Count Comparison

	Part Number	Single Phase	Part Number	Dual Phase
MOSFETs	CSD18531Q5A	2	CSD18531Q5A	4
C_{in}	25 V Ceramic	1	25 V Ceramic	1
C_{out}	PCV1E391MCL2GS	2	PCV1E391MCL2GS	1
Inductor	XAL1580-302	1	SER1390-153	2
IC	LM5122	1	LM5122	2
R_{sense}	2 W Current Sense	1	2 W Current Sense	2
Total		8		12

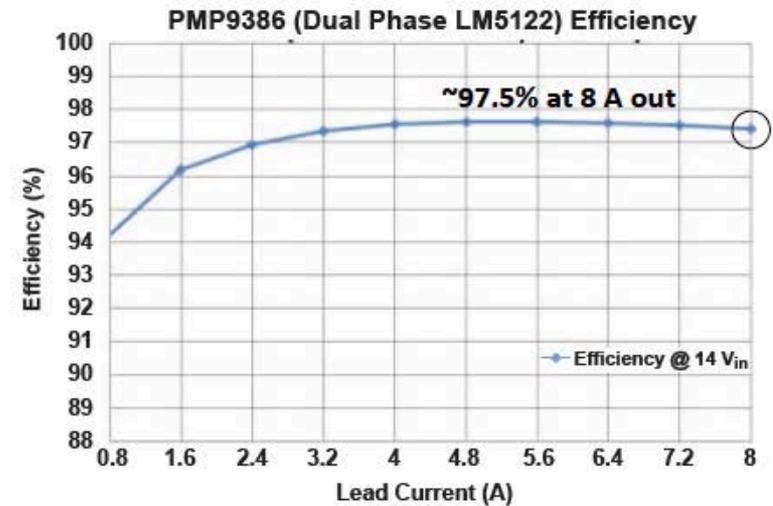
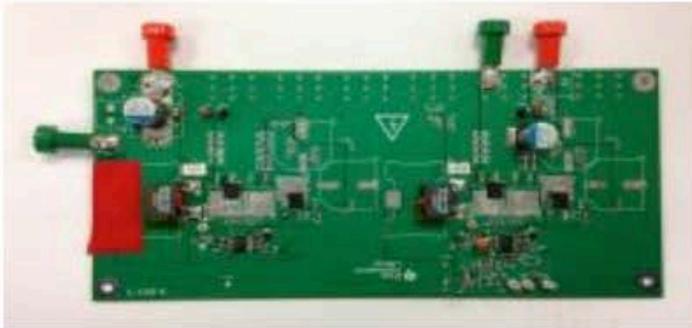
Bench Test Results: Single Phase (PMP9385)

Efficiency and Thermals Comparison



Bench Test Results: Dual Phase (PMP9386)

Efficiency and Thermals Comparison



Conclusion

- Using equations and step-by-step approach provided herein enables designer to adjust design for optimizing efficiency or size
- Both size, cost and performance can be modified by using multiphase boost approach
- Thermal performance improved using two phase approach
 - Thermal stress on FETs significantly reduced with multiphase approach
- For single phase boost
 - Increasing switching frequency in an attempt to reduce size will result in exceeding FET thermal limits
- For two phase boost
 - Increasing switching frequency is feasible without thermal stress on FETs
 - Significant reduction in size can be further gained

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